DESCRIPTION

The 2SB1197KX is available in SOT-23 package.

FEATURES

High current capacity in compact package.

 $I_{C} = -0.8A$

Epitaxial planar type

NPN complement: 2SD1781KX

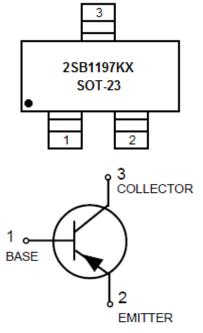
RoHS Compliant

Available in SOT-23 package

ORDERING INFORMATION

Package Type	Part Number				
SOT-23	2SB1197KQ				
	2SB1197KR				
Note	3,000pcs/ Reel				
AiT provides all RoHS Compliant Products					

PIN DESCRIPTION



ABSOLUTE MAXIMUM RATINGS

$T_A = 25^{\circ}C$

··	
V _{CBO} , Collector-base voltage	-40V
V _{CEO} , Collector-emitter voltage	-32V
V _{EBO} , Emitter-base voltage	-5V
Ic, Collector current	-0.8A
Pc, Collector power dissipation	0.2W
T _J , Junction temperature	150°C
T _{STG} , Storage temperature	-55°C ~ 150°C

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

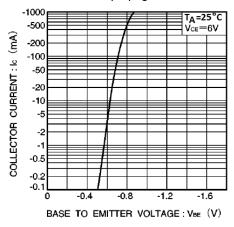
ELECTRICAL CHARACTERISTICS

 $T_A = 25^{\circ}C$

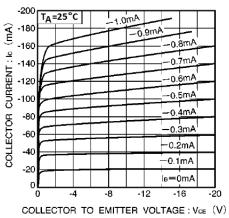
Parameter	Symbol	Conditions		Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	ВУсво	I _C = -50μA		-40	-	-	V
Collector-emitter breakdown voltage	BV _{CEO}	I _C = -1mA		-32	-	-	V
Emitter-base breakdown voltage	BV _{EBO}	I _E = -50μA		-5	-	-	V
Collector cutoff current	Ісво	V _{CB} = -20V		-	-	-0.5	μΑ
Emitter cutoff current	I _{EBO}	V _{EB} = -4V		-	-	-0.5	μΑ
Collector-emitter saturation voltage	V _{CE(SAT)}	Ic / IB = -0.5A / -50mA		-	-	-0.5	V
DC current transfer ratio	h _{FE}	V _{CE} = -3V,	Q	120	-	270	-
		Ic= -100mA	R	180	-	390	-
Transition frequency	fr	Vce =-5V, Ie= 50mA, f=100MHz		-	200	-	MHz
Output capacitance	Cob	V _{CB} = -10V, I _E =0A, f=1MHz		-	12	30	pF

TYPICAL PERFORMANCE CHARACTERISTICS

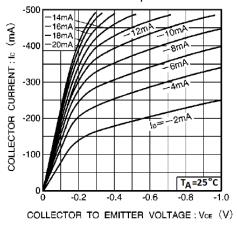
Figuer1. Grounded emitter propagation characteristics



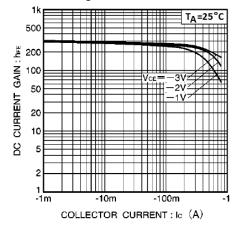
Figuer2. Grounded emitter output characteristics(I)



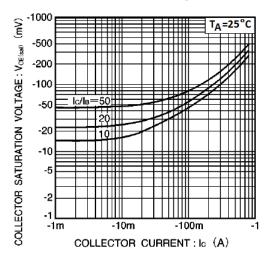
Figuer3. Grounded emitter output characteristics(II)



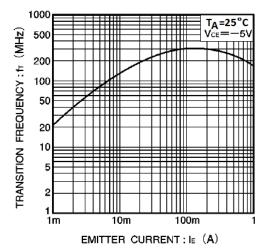
Figuer4. DC current gain vs. collector current



Figuer5. Collector-emitter saturation voltage vs. collector current

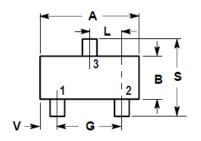


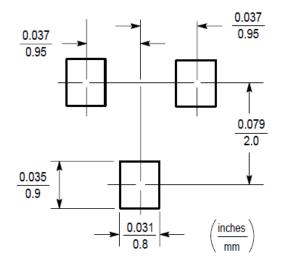
Figuer6. Gain bandwidth product vs. emitter current

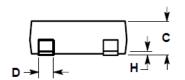


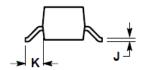
PACKAGE INFORMATION

Dimension in SOT-23 Package (Unit: mm)









DIM	MILLIN	METERS	INCHES		
	MIN	MAX	MIN	MAX	
А	2.80	3.04	0.1102	0.1197	
В	1.20	1.40	0.0472	0.0551	
С	0.89	1.11	0.0350	0.0440	
D	0.37	0.50	0.0150	0.0200	
G	1.78	2.04	0.0701	0.0807	
Н	0.013	0.100	0.0005	0.0040	
J	0.085	0.177	0.0034	0.0070	
K	0.35	0.69	0.0140	0.0285	
L	0.89	1.02	0.0350	0.0401	
S	2.10	2.64	0.0830	0.1039	
V	0.45	0.60	0.0177	0.0236	

IMPORTANT NOTICE

AiT Semiconductor Inc. (AiT) reserves the right to make changes to any its product, specifications, to discontinue any integrated circuit product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

AiT Semiconductor Inc.'s integrated circuit products are not designed, intended, authorized, or warranted to be suitable for use in life support applications, devices or systems or other critical applications. Use of AiT products in such applications is understood to be fully at the risk of the customer. As used herein may involve potential risks of death, personal injury, or servere property, or environmental damage. In order to minimize risks associated with the customer's applications, the customer should provide adequate design and operating safeguards.

AiT Semiconductor Inc. assumes to no liability to customer product design or application support. AiT warrants the performance of its products of the specifications applicable at the time of sale.